## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Thomas A. Figura, Kevin G. Donohoe, and Thomas Dunbar

§ Group Art Unit:

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8 8 8

Serial No.:

Examiner:

Filed:

December 22, 1999

Atty. Docket:

94-0280.04

For:

USE OF A PLASMA SOURCE TO FORM A LAYER

DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

3-2-00 Linds B.

## INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents Washington, D.C. 20231

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Signature

In compliance with the duty of disclosure under 37 C.F.R. § 1.56, Applicants respectfully request that this Information Disclosure Statement be entered and that the references listed on the attached Form PTO-1449 be considered by the Examiner and made of record. Copies of the listed references are enclosed for the convenience of the Examiner.

In accordance with 37 C.F.R. § 1.97(b), this Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possible material information as defined in 37 C.F.R. § 1.56(a) exists.

The following references are submitted for the Examiner's review:

## U.S. Patents

U.S. Patent No.	Issue Date	Inventor
5,821,621	10/13/98	Jeng
5,804,259	09/08/98	Robles
5,496,773	03/05/96	Rhodes et al.
5,486,493	01/23/96	Jeng
5,476,817	12/19/95	Numata
5,443,941	08/22/95	Bariya et al.
5,422,310	06/06/95	Ito
5,422,294	06/06/95	Noble, Jr.
5,382,316	01/17/95	Hills et al.

5,364,817	11/15/94	Lur et al.
5,364,809	11/15/94	Kwon et al.
5,354,715	10/11/94	Wang et al.
5,326,431	07/05/94	Kadomura
5,312,773	05/17/94	Nagashima
5,292,677	03/08/94	Dennison
5,286,675	02/15/94	Chen et al.
5,284,787	02/08/94	Ahn
5,232,509	08/03/93	Min et al.
5,185,282	02/09/93	Lee et al.
5,162,248	11/10/92	Dennison et al.
5,150,276	09/22/92	Gonzalez et al.
5,110,712	05/05/92	Kessler et al.
5,096,849	03/17/92	Beilstein, Jr. et al.
5.084,413	01/28/92	Fujita et al.
5,066,607	11/19/91	Banerjee
4,918,033	04/17/90	Bartha et al.
4,797,373	01/10/89	Malhi et al.
4,759,958	07/26/88	Numata et al.

## Other References

Tetsuo Ono, Ryoji Hamasaki and Tatsumi Mizutani, "Mechanism for CF Polymer Film Deposition through Deep SiO₂ Holes in Electron Cyclotron Resonance Plasma," Jpn. J. Appl. Phys. Vol. 35, pp. 2468-2471, Part 1, No. 4B, April 1996.

Ephrath, L. M., "Teflon Polymer Mask For RIE of Contact Roles," IBM Technical Disclosure Bulletin, Vol. 25, No. 9, pp. 4587-4588, February 1983.

As this information is being submitted within three months of the date of filing of the application, Applicants understand that no fee or certification is required for the submission and consideration of this information at this time.

If there are any matters which may be resolved or clarified through telephone interview, the Examiner is respectfully requested to contact Applicants' undersigned attorney at the number indicated.

A Form PTO-1449 is enclosed herewith.

Respectfully submitted,

Date: 1424 49

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